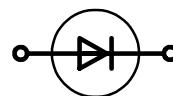


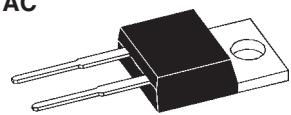
# HiPerFRED™ Epitaxial Diode with soft recovery

**I<sub>FAV</sub>** = 30 A  
**V<sub>RRM</sub>** = 300 V  
**t<sub>rr</sub>** = 30 ns

V <sub>RSM</sub> V	V <sub>RRM</sub> V	Type
300	300	DSEP 29-03A



TO-220 AC



A = Anode, C = Cathode, TAB = Cathode

Symbol	Conditions	Maximum Ratings		Features
I <sub>FRMS</sub>		35	A	
I <sub>FAVM</sub>	T <sub>C</sub> = 145°C; rectangular, d = 0.5	30	A	
I <sub>FSM</sub>	T <sub>VJ</sub> = 45°C; t <sub>p</sub> = 10 ms (50 Hz), sine	300	A	
E <sub>AS</sub>	T <sub>VJ</sub> = 25°C; non-repetitive I <sub>AS</sub> = 3 A; L = 180 µH	1.2	mJ	
I <sub>AR</sub>	V <sub>A</sub> = 1.5·V <sub>R</sub> typ.; f = 10 kHz; repetitive	0.3	A	
T <sub>VJ</sub>		-55...+175	°C	
T <sub>VJM</sub>		175	°C	
T <sub>stg</sub>		-55...+150	°C	
P <sub>tot</sub>	T <sub>C</sub> = 25°C	165	W	
M <sub>d</sub>	mounting torque	0.4...0.6	Nm	
Weight	typical	2	g	

## Applications

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode in converters and motor control circuits
- Rectifiers in switch mode power supplies (SMPS)
- Inductive heating
- Uninterruptible power supplies (UPS)
- Ultrasonic cleaners and welders

Symbol	Conditions	Characteristic Values		Features
		typ.	max.	
I <sub>R</sub> ①	V <sub>R</sub> = V <sub>RRM</sub> ; T <sub>VJ</sub> = 25°C T <sub>VJ</sub> = 150°C	10 1	µA mA	
V <sub>F</sub> ②	I <sub>F</sub> = 30 A; T <sub>VJ</sub> = 150°C T <sub>VJ</sub> = 25°C	0.93 1.26	V V	
R <sub>thJC</sub> R <sub>thCH</sub>		0.5	0.9 K/W	
t <sub>rr</sub>	I <sub>F</sub> = 1 A; -di/dt = 200 A/µs; V <sub>R</sub> = 30 V; T <sub>VJ</sub> = 25°C	30	ns	
I <sub>RM</sub>	V <sub>R</sub> = 100 V; I <sub>F</sub> = 50 A; -di <sub>F</sub> /dt = 100 A/µs T <sub>VJ</sub> = 100°C	7	A	

Pulse test: ① Pulse Width = 5 ms, Duty Cycle < 2.0%  
② Pulse Width = 300 µs, Duty Cycle < 2.0%

Data according to IEC 60747 and per diode unless otherwise specified

**Recommended replacement:**  
**DPG30I300PA**

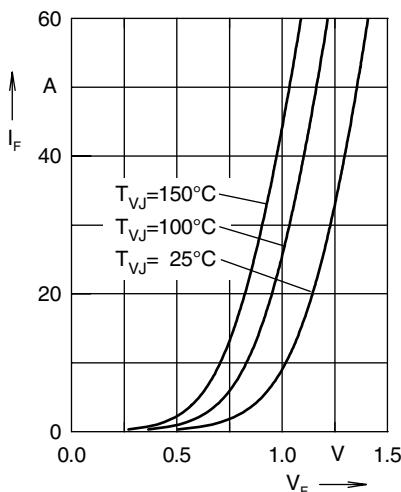
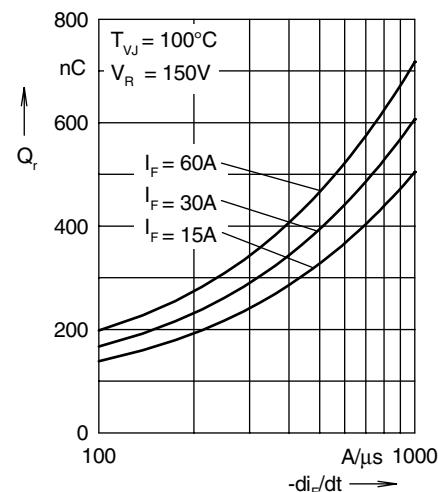
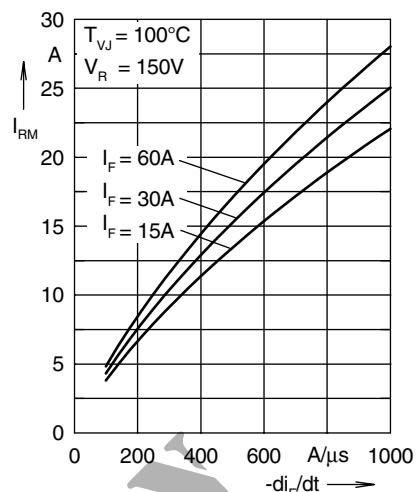
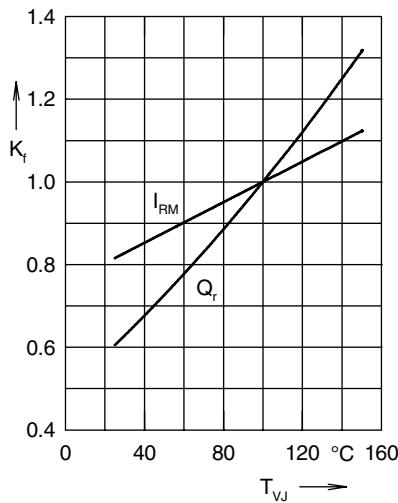
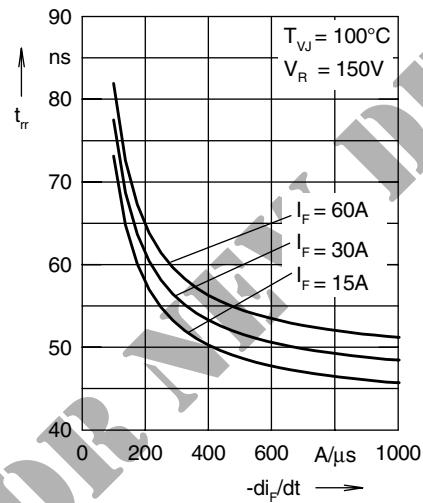
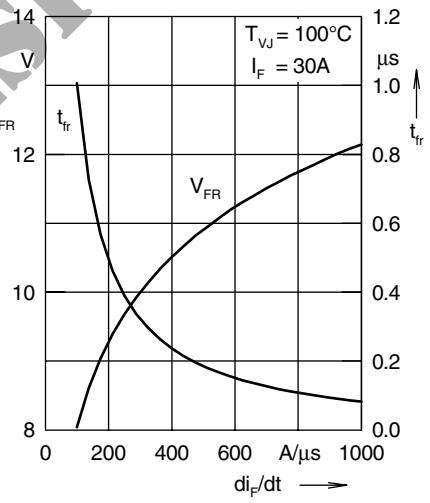
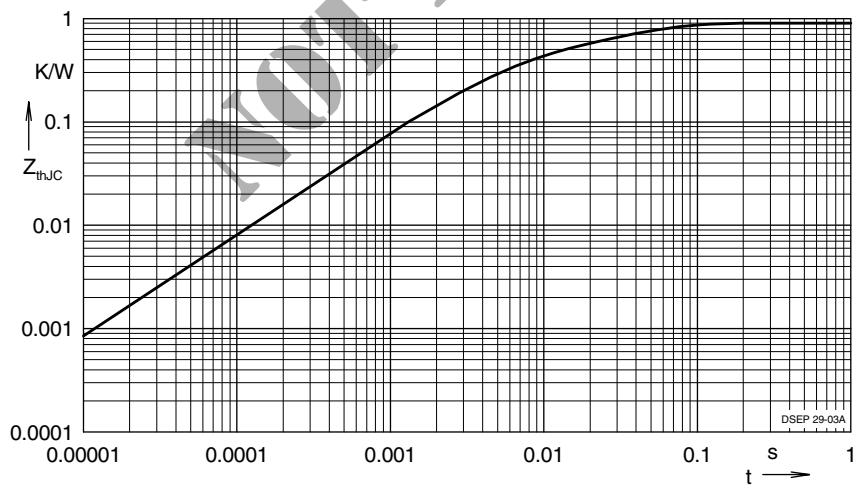
Fig. 1 Forward current  $I_F$  versus  $V_F$ Fig. 2 Reverse recovery charge  $Q_r$  versus  $-di_F/dt$ Fig. 3 Peak reverse current  $I_{RM}$  versus  $-di_F/dt$ Fig. 4 Dynamic parameters  $Q_r$ ,  $I_{RM}$  versus  $T_{VJ}$ Fig. 5 Recovery time  $t_{rr}$  versus  $-di_F/dt$ Fig. 6 Peak forward voltage  $V_{FR}$  and  $t_{tr}$  versus  $di_F/dt$ 

Fig. 7 Transient thermal resistance junction to case

Constants for  $Z_{thJC}$  calculation:

i	$R_{thi}$ (K/W)	$t_i$ (s)
1	0.502	0.005
2	0.193	0.0003
3	0.205	0.016

NOTE: Fig. 2 to Fig. 6 shows typical values